



## ISC Audits & Reviews SC Summary February 2016

| Doc. #     | Title  | Results |
|------------|--|---------|
| 5478;      | <b>New Standard: Test Method for Thin-film Silicon PV Modules Light Soaking;</b>   | Passed  |
| 5564C;     | <b>New Standard: Test Method for the Measurement of Chlorine in Silicon by Ion Chromatography;</b>   | Passed  |
| 5621C;     | <b>Preliminary Standard: Guide for Determining the Quality of Ion Exchanged Resin Used in Polish Applications of Ultrapure Water System;</b>   | Passed  |
| 5829A      | <b>Line Item Revision to SEMI E171-0515 “Specification for Predictive Carrier Logistics (PCL)” and SEMI E171.1-0515 “Specification for SECS-II Protocol for Predictive Carrier Logistics”</b>  |         |
| 5829A-LI1; | Improve expression of CFJ Event definition;  | Passed  |
| 5829A-LI2; | Improve CLJ Event definition;  | Passed  |
| 5829A-LI3; | Add ‘Object’ to the reference in the section 8.1.1 of E171;  | Passed  |
| 5829A-LI4; | Correct editorial errors in Table 14 and Table 16 of E171;   | Passed  |
| 5829A-LI5; | Add CarrierFlowID and CLJLPID to Table 8 CLJ SECS-II Attribute Definitions of E171.1;  | Passed  |
| 5829A-LI6; | Improve definition of the response to AMHSArrivalInfo service in E171;   | Passed  |
| 5855A      | <b>Line Item Revision of SEMI MF1771-1110 Test Method For Evaluating Gate Oxide Integrity By Voltage Ramp Technique</b>  |         |
| 5855A-LI1; | Correct the source and its designations for the referenced standards in section 4.2;   | Passed  |
| 5888;      | <b>Revision to SEMI E170-0815: Specification for Production Recipe Cache (PRC) with title change to Specification for Secured Foundation of Recipe Management System (SFORMS), SEMI E170.1-0815: Specification for SECS-II Protocol for Production Recipe Cache with title change to Specification for SECS-II Protocol for Secured Foundation of Recipe Management System (SFORMS);</b> | Passed  |
| 5890;      | <b>Revision to SEMI T7-0415 Specification for Back Surface Marking Of Double-Side Polished Wafers With A Two-Dimensional Matrix Code Symbol</b>  | Passed  |
| 5893;      | <b>Revision of SEMI M1-0915 Specification for Polished Single Crystal Silicon Wafers;</b>  | Passed  |
| 5910       | <b>Line Item Revision of SEMI M57-0515, Specifications for Silicon Annealed Wafers</b>   |         |
| 5910-LI1;  | Correct the title of this standard from “Specifications” to “Specification”;   | Passed  |



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|---------------|--|----------------|
| <b>5929</b>   | <b>Line Item Revision of SEMI MF42-1105 (Reapproved 0611) Test Methods for Conductivity Type of Extrinsic Semiconducting Materials</b>   |                |
| 5929-LI1;     | Correct the title of this standard from “Test Methods” to “Test Method”;   | Passed         |
| <b>5930</b>   | <b>Line Item Revision of SEMI MF43-0705 (Reapproved 0611) Test Methods for Resistivity of Semiconductor Materials</b>  |                |
| 5930-LI1;     | Correct the title of this standard from “Test Methods” to “Test Method”;   | Passed         |
| <b>5931;</b>  | <b>Reapproval of SEMI MF81-1105 (Reapproved 0611) Test Method for Measuring Radial Resistivity Variation on Silicon Wafers ;</b>   | Passed         |
| <b>5932;</b>  | <b>Reapproval of SEMI MF154-1105 (Reapproved 0611) Guide for Identification of Structures and Contaminants Seen on Specular Silicon Surfaces ;</b>   | Passed         |
| <b>5933</b>   | <b>Line Item Revision of SEMI MF674-0705 (Reapproved 0611) Practice for Preparing Silicon for Spreading Resistance Measurements</b>  |                |
| 5933-LI1;     | Correct the title of this standard from “Practices” to “Practice”;   | Passed         |
| <b>5934</b>   | <b>Line Item Revision of SEMI MF847-0705 (Reapproved 0611) Test Method for Measuring Crystallographic Orientation of Flats on Single Crystal Silicon Wafers by X-Ray Techniques</b>                |                |
| 5934-LI1;     | Correct the title of this standard from “Test Methods” to “Test Method”;   | Passed         |
| <b>5935;</b>  | <b>Reapproval of SEMI MF951-0305 (Reapproved 0211) Test Method for Determination of Radial Interstitial Oxygen Variation in Silicon Wafers ;</b>   | Passed         |
| <b>5936</b>   | <b>Line Item Revision to SEMI MF1152-0305 (Reapproved 0211) Test Methods for Dimensions of Notches on Silicon Wafers</b>   |                |
| 5936-LI1;     | Correct the title of this standard from “Test Methods” to “Test Method”;   | Passed         |
| <b>5937;</b>  | <b>Reapproval of SEMI MF1239-0305 (Reapproved 0211) Test Method for Oxygen Precipitation Characteristics of Silicon Wafers by Measurement of Interstitial Oxygen Reduction ;</b>                   | Passed         |
| <b>5938;</b>  | <b>Reapproval of SEMI MF2139-1103 (Reapproved 1110) Test Method for Measuring Nitrogen Concentration in Silicon Substrates by Secondary Ion Mass Spectrometry ;</b>                                | Passed         |
| <b>5939;</b>  | <b>Reapproval of SEMI MF1617-0304 (Reapproved 0710) Test Method for Measuring Surface Sodium, Aluminum, Potassium, and Iron on Silicon and EPI Substrates by Secondary Ion Mass Spectrometry ;</b> | Passed         |



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|--------|---|---------|
| 5940;  | Reapproval of SEMI MF533-0310 Test Method for Thickness and Thickness Variation of Silicon Wafers ; | Passed  |

Line Item (LI)

For more information, please contact the SEMI Standards Engineer/Coordinator (<http://www.semi.org/standards/contacts>) nearest you.

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Feb 1, 2016*